

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1178448	(semiconductor silicon si gaas) with (substrate carrier layer board structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:19
L2	165781	(thru via hole though throughhole opening) with 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:20
L3	263399	(thru via hole through throughhole opening) with 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:20
L4	3689	(elongat\$4 annular\$4 rectang\$4) with 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:21
L5	2026	(chip die dice ic (integrated adj circuit)) and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:22
L6	731	(cte match\$4 (co adj efficient) coefficient therm expansion) and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:23

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L6	1178448	(semiconductor silicon si gaas) with (substrate carrier layer board structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:40
L7	263399	(thru via hole through throughhole opening) with L6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:41
L8	263399	(thru via hole through throughhole opening) with 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:42
L9	21332	(annular core) and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:42
L10	9262	(annular\$4) and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:43
L11	5540	(chip die dice ic (integrated adj circuit)) and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:43
L12	3745	(cte match\$4 (co adj efficient) coefficient thermal expansion) and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:45
L13	680	12 and (elastic\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 16:07

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L12	3745	(cte match\$4 (co adj efficient) coefficient thermal expansion) and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 15:45
L13	680	12 and (elastic\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 16:07